

FORM PTO - 1449 SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT					ATTY DOCKET NO.: ASC-025DV1C1 APPLICANT(S): Cheng <i>et al.</i> SERIAL NO.: 10/802,185 FILING DATE: March 17, 2004 GROUP: 2813				
U.S. PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
CAT	A236	4,969,031	11/00/1990	Kobayashi <i>et al.</i>					
CAT	A237	5,439,843	08/08/1995	Sakaguchi <i>et al.</i>					
CAT	A238	5,548,128	08/20/1996	Soref <i>et al.</i>					
CAT	A239	5,607,876	03/04/1997	Biegelsen <i>et al.</i>					
CAT	A240	6,489,639	12/03/2002	Hoke <i>et al.</i>					
CAT	A241	6,591,321	07/08/2003	Arimilli <i>et al.</i>			11/09/1999		
CAT	A242	6,597,016	07/22/2003	Yuki <i>et al.</i>			01/13/2000		
CAT	A243	6,646,322	11/11/2003	Fitzgerald			07/16/2001		
CAT	A244	6,674,150	01/06/2004	Takagi <i>et al.</i>			04/23/2002		
CAT	A245	6,677,192	01/13/2004	Fitzgerald			07/16/2001		
CAT	A246	6,703,144	03/09/2004	Fitzgerald			03/18/2003		
CAT	A247	6,703,688	03/09/2004	Fitzgerald			7/16/2001		
CAT	A248	6,737,670	05/18/2004	Cheng <i>et al.</i>			03/07/2003		
CAT	A249	6,750,130	01/07/2001	Fitzgerald			01/07/2001		
CAT	A250	2002/0084000	07/04/2002	Fitzgerald			12/17/2001		
CAT	A251	2003/0215990	11/20/2003	Fitzgerald <i>et al.</i>			03/14/2003		
CAT	A252	2004/0075149	04/22/2004	Fitzgerald <i>et al.</i>			07/23/2003		
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB. CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
CAT	B45	61-141116	06/28/1986	JP				N	Y (abstract only)
CAT	B46	2-210816	08/22/1990	JP				N	Y (abstract only)
CAT	B47	3-036717	02/18/1991	JP				N	Y
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U.S. PATENT DOCUMENTS									
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✓		✓		✓	✓		✓		
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
✓		✓			✓		✓	✓	✓
EXAM. OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)									
CAT	C99	Grillot <i>et al.</i> , "Acceptor diffusion and segregation in $(Al_xGa_{1-x})_{0.5}In_{0.5}P$ heterostructures," <u>Journal of Applied Physics</u> , Vol. 91, No. 8 (2002), pp. 4891-4899.							
CAT	C100	Halsall <i>et al.</i> , "Electron diffraction and Raman studies of the effect of substrate misorientation on ordering in the AlGaNp system," <u>Journal of Applied Physics</u> , Vol. 85, No. 1 (1999), pp. 199-202.							
CAT	C101	Hsu <i>et al.</i> , "Surface morphology of related Ge_xSi_{1-x} films," <u>Appl. Phys. Lett.</u> , Vol. 61, No. 11 (1992), pp. 1293-1295							
EXAMINER <u>Craig A. Thompson</u>					DATE CONSIDERED <u>12/28/04</u>				

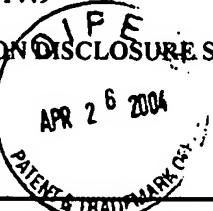
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U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
CAT	A1	4,010,045	03/01/1977	Ruehrwein			
CAT	A2	4,704,302	11/03/1987	Bruel et al.			
CAT	A3	4,710,788	12/01/1987	Dämbkes et al.			
CAT	A4	4,987,462	01/22/1991	Kim et al.			
CAT	A5	4,990,979	02/05/1991	Otto			
CAT	A6	4,997,776	03/05/1991	Harame et al.			
CAT	A7	5,013,681	05/07/1991	Godbey et al.			
CAT	A8	5,155,571	10/13/1992	Wang et al.			
CAT	A9	5,166,084	11/24/1992	Pfiester			
CAT	A10	5,177,583	01/05/1993	Endo et al.			
CAT	A11	5,202,284	04/13/1993	Kamins et al.			
CAT	A12	5,207,864	05/04/1993	Bhat et al.			
CAT	A13	5,208,182	05/04/1993	Narayan et al.			
CAT	A14	5,212,110	05/18/1993	Pfiester et al.			
CAT	A15	5,221,413	06/22/1993	Brasen et al.			
CAT	A16	5,240,876 A	08/31/1993	Gaul et al.			
CAT	A17	5,241,197	08/31/1993	Murakami et al.			
CAT	A18	5,250,445	10/05/1993	Bean et al.			
CAT	A19	5,285,086	02/08/1994	Fitzgerald			
CAT	A20	5,291,439	03/01/1994	Kauffmann et al.			
CAT	A21	5,298,452	03/29/1994	Meyerson			
CAT	A22	5,310,451	05/10/1994	Tejwani et al.			
CAT	A23	5,316,958	05/31/1994	Meyerson			
CAT	A24	5,346,848	09/13/1994	Grupen-Shemansky et al.			
CAT	A25	5,374,564	12/20/1994	Bruel			
CAT	A26	5,399,522	03/21/1995	Ohori			
CAT	A27	5,413,679	05/09/1995	Godbey			
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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
CAT	A28	5,424,243	06/13/1995	Takasaki			
CAT	A29	5,426,069	06/20/1995	Selvakumar et al.			
CAT	A30	5,426,316	06/20/1995	Mohammad			
CAT	A31	5,442,205	08/15/1995	Brasen et al.			
CAT	A32	5,461,243	10/24/1995	Ek et al.			
CAT	A33	5,461,250	10/24/1995	Burghartz et al.			
CAT	A34	5,462,883	10/31/1995	Dennard et al.			
CAT	A35	5,476,813	12/19/1995	Naruse			
CAT	A36	5,479,033	12/26/1995	Baca et al.			
CAT	A37	5,484,664	01/16/1996	Kitahara et al.			
CAT	A38	5,523,243	06/04/1996	Mohammad			
CAT	A39	5,523,592	06/04/1996	Nakagawa et al.			
CAT	A40	5,534,713	07/09/1996	Ismail et al.			
CAT	A41	5,536,361	07/16/1996	Kondo et al.			
CAT	A42	5,540,785	07/30/1996	Dennard et al.			
CAT	A43	5,596,527	01/21/1997	Tomioka et al.			
CAT	A44	5,617,351	04/01/1997	Bertin et al.			
CAT	A45	5,630,905	05/20/1997	Lynch et al.			
CAT	A46	5,659,187	08/19/1997	Legoues et al.			
CAT	A47	5,683,934	11/04/1997	Candelaria			
CAT	A48	5,698,869	12/16/1997	Yoshimi et al.			
CAT	A49	5,714,777	02/03/1998	Ismail et al.			
CAT	A50	5,728,623	03/17/1998	Mori			
CAT	A51	5,739,567	04/14/1998	Wong			
CAT	A52	5,759,898	06/02/1998	Ek et al.			
CAT	A53	5,777,347	07/07/1998	Bartelink			
CAT	A54	5,786,612	07/28/1998	Otani et al.			

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U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
CAT	A55	5,786,614	07/28/1998	Chuang et al.			
CAT	A56	5,792,679	08/11/1998	Nakato			
CAT	A57	5,808,344	09/15/1998	Ismail et al.			
CAT	A58	5,847,419	12/08/1998	Imai et al.			
CAT	A59	5,863,830	01/26/1999	Bruel et al.			
CAT	A60	5,877,070	03/02/1999	Goesele et al.			
CAT	A61	5,882,987	03/16/1999	Srikrishnan			
CAT	A62	5,891,769	04/06/1999	Hong et al.			
CAT	A63	5,906,708	05/25/1999	Robinson et al.			
CAT	A64	5,906,951	05/25/1999	Chu et al.			
CAT	A65	5,912,479	06/15/1999	Mori et al.			
CAT	A66	5,943,560	08/24/1999	Chang et al.			
CAT	A67	5,963,817	10/05/1999	Chu et al.			
CAT	A68	5,966,622	10/12/1999	Levine et al.			
CAT	A69	5,993,677	11/30/1999	Biasse et al.			
CAT	A70	5,998,807	12/07/1999	Lustig et al.			
CAT	A71	6,013,134	01/11/2000	Chu et al.			
CAT	A72	6,013,563	01/11/2000	Henley et al.			
CAT	A73	6,020,252	02/01/2000	Aspar et al.			
CAT	A74	6,033,974	03/07/2000	Henley et al.			
CAT	A75	6,033,995	03/07/2000	Muller			
CAT	A76	6,058,044	05/02/2000	Sugiura et al.			
CAT	A77	6,059,895	05/09/2000	Chu et al.			
CAT	A78	6,074,919	06/13/2000	Gardner et al.			
CAT	A79	6,096,590	08/01/2000	Chan et al.			
CAT	A80	6,103,559	08/15/2000	Gardner et al.			
CAT	A81	6,103,597	08/15/2000	Aspar et al.			
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U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
CAT	A82	6,103,599	08/15/2000	Henley et al.			
CAT	A83	6,107,653	08/22/2000	Fitzgerald			
CAT	A84	6,111,267	08/29/2000	Fischer et al.			
CAT	A85	6,117,750	09/12/2000	Bensahel et al.			
CAT	A86	6,130,453	10/10/2000	Mei, et al.			
CAT	A87	6,133,799	10/17/2000	Favors Jr., et al.			
CAT	A88	6,140,687	10/31/2000	Shimomura et al.			
CAT	A89	6,143,636	11/07/2000	Forbes et al.			
CAT	A90	6,153,495	11/28/2000	Kub et al.			
CAT	A91	6,154,475	11/28/2000	Soref et al.			
CAT	A92	6,160,303	12/12/2000	Fattaruso			
CAT	A93	6,162,688	12/19/2000	Gardner et al.			
CAT	A94	6,162,705	12/19/2000	Henley et al.			
CAT	A95	6,184,111	02/06/2001	Henley et al.			
CAT	A96	6,190,998 B1	02/20/2001	Bruel et al.			
CAT	A97	6,191,007	02/20/2001	Matsui et al.			
CAT	A98	6,191,432	02/20/2001	Sugiyama et al.			
CAT	A99	6,194,722	02/27/2001	Howe et al.			
CAT	A100	6,204,529	03/20/2001	Lung, et al.			
CAT	A101	6,207,977	03/27/2001	Augusto			
CAT	A102	6,210,988	04/03/2001	Howe et al.			
CAT	A103	6,218,677	04/17/2001	Broekaert			
CAT	A104	6,225,192 B1	05/01/2001	Aspar et al.			
CAT	A105	6,232,138	05/15/2001	Fitzgerald et al.			
CAT	A106	6,235,567	05/22/2001	Huang			
CAT	A107	6,242,324	06/05/2001	Kub et al.			
CAT	A108	6,249,022	06/19/2001	Lin, et al.			
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		GROUP: Not yet assigned 2813

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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
CAT	A109	6,251,751 B1	06/26/2001	Chu et al.			
CAT	A110	6,251,755	06/26/2001	Furukawa et al.			
CAT	A111	6,261,929	07/17/2001	Gehrke et al.			
CAT	A112	6,266,278	07/24/2001	Harari, et al.			
CAT	A113	6,271,551	08/07/2001	Schmitz et al.			
CAT	A114	6,271,726	08/07/2001	Fransis et al.			
CAT	A115	6,290,804 B1	09/18/2001	Henley et al.			02/20/1998
CAT	A116	6,291,321	09/18/2001	Fitzgerald			03/09/1999
CAT	A117	6,303,468 B1	10/16/2001	Aspar et al.			10/16/2001
CAT	A118	6,313,016	11/06/2001	Kibbel et al.			12/22/1999
CAT	A119	6,316,301	11/13/2001	Kant			03/08/2000
CAT	A120	6,323,108	11/27/2001	Kub et al.			07/27/1999
CAT	A121	6,326,667 B1	12/04/2001	Sugiyama et al.			09/08/2000
CAT	A122	6,329,063	12/11/2001	Lo et al.			12/11/1998
CAT	A123	6,335,546	01/01/2002	Tsuda et al.			07/30/1999
CAT	A124	6,339,232	01/15/2002	Takagi			09/20/1999
CAT	A125	6,344,417 B1	02/05/2002	Usenko			08/08/2000
CAT	A126	6,346,459 B1	02/12/2002	Usenko et al.			02/02/2000
CAT	A127	6,350,993	02/26/2002	Chu et al.			03/12/1999
CAT	A128	6,352,909 B1	03/05/2002	Usenko			05/26/2000
CAT	A129	6,355,493 B1	03/12/2002	Usenko			06/30/2000
CAT	A130	6,368,733	04/09/2002	Nishinaga			08/05/1999
CAT	A131	6,368,938 B1	04/09/2002	Usenko			06/07/2000
CAT	A132	6,369,438 B1	04/09/2002	Sugiyama et al.			12/22/2000
CAT	A133	6,372,356	04/16/2002	Thornton et al.			04/28/2000
CAT	A134	6,372,593 B1	04/16/2002	Hattori et al.			07/19/2000
CAT	A135	6,372,609 B1	04/16/2002	Aga et al.			10/08/1999

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U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
CAT	A136	6,387,829 B1	05/14/2002	Usenko et al.			04/06/2000
CAT	A137	6,391,740 B1	05/21/2002	Cheung et al.			04/28/1999
CAT	A138	6,399,970	06/04/2002	Kubo et al.			09/19/1997
CAT	A139	6,403,975	06/11/2002	Brunner et al.			04/08/1997
CAT	A140	6,407,406	06/18/2002	Tezuka			06/29/1999
CAT	A141	6,410,371 B1	06/25/2002	Yu et al.			02/26/2001
CAT	A142	6,425,951	07/30/2002	Chu et al.			08/06/1999
CAT	A143	6,429,061	08/06/2002	Rim			07/26/2000
CAT	A144	6,445,016 B1	09/03/2002	An et al.			02/28/2001
CAT	A145	6,448,152 B1	09/10/2002	Henley et al.			07/16/2001
CAT	A146	6,455,397 B1	09/24/2002	Belford			11/09/2000
CAT	A147	6,458,672 B1	10/01/2002	Henley et al.			11/02/2000
CAT	A148	6,475,072 B1	11/05/2002	Canaperi et al.			09/29/2000
CAT	A149	6,514,836 B2	02/04/2003	Belford			06/04/2001
CAT	A150	6,515,335 B1	02/04/2003	Christiansen et al.			01/04/2002
CAT	A151	6,521,041	02/18/2003	Wu et al.			04/09/1999
CAT	A152	6,524,935 B1	02/25/2003	Canaperi et al.			09/29/2000
CAT	A153	6,534,381 B2	03/18/2003	Cheung et al.			01/04/2000
CAT	A154	6,555,839	04/29/2003	Fitzgerald et al.			05/16/2001
CAT	A155	6,573,126	06/03/2003	Cheng et al.			08/10/2001
CAT	A156	6,583,015	06/24/2003	Fitzgerald et al.			08/06/2001
CAT	A157	6,583,437 B2	06/24/2003	Mizuno et al.			03/19/2001
CAT	A158	6,593,191	07/15/2003	Fitzgerald			05/16/2001
CAT	A159	6,593,625 B2	07/15/2003	Christiansen et al.			04/03/2002
CAT	A160	6,596,610 B1	07/22/2003	Kuwabara et al.			11/27/2000
CAT	A161	6,602,613	08/05/2003	Rim			01/17/2001
CAT	A162	6,603,156	08/05/2003	Fitzgerald			03/31/2001
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U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
CAT	A163	6,607,948 B1	08/19/2003	Sugiyama et al.			08/24/2001
CAT	A164	6,624,047 B1	09/23/2003	Sakaguchi et al.			02/01/2000
CAT	A165	6,624,478 B2	09/23/2003	Anderson et al.			01/30/2002
CAT	A166	6,632,724 B2	10/14/2003	Henley et al.			01/13/2000
CAT	A167	6,635,909 B2	10/21/2003	Clark et al.			03/19/2002
CAT	A168	6,645,831 B1	11/11/2003	Shaheen et al.			05/07/2002
CAT	A169	6,649,492 B2	11/18/2003	Chu et al.			02/11/2002
CAT	A170	6,656,271 B2	12/02/2003	Yonchara et al.			12/03/1999
CAT	A171	6,664,169 B1	12/16/2003	Iwasaki et al.			06/05/2000
CAT	A172	6,677,183 B2	01/13/2004	Sakaguchi et al.			01/31/2002
CAT	A173	6,680,240 B1	01/20/2004	Maszara			06/25/2002
CAT	A174	6,680,260 B2	01/20/2004	Akiyama et al.			09/17/2002
CAT	A175	6,690,043 B1	02/10/2004	Usuda et al.			11/22/2000
CAT	A176	6,706,614 B1	03/16/2004	An et al.			05/15/2002
CAT	A177	6,706,618 B2	03/16/2004	Takisawa et al.			07/29/2002
CAT	A178	6,707,106 B1	03/16/2004	Wristers et al.			10/18/2002
CAT	A179	6,709,903 B2	03/23/2004	Christiansen et al.			04/30/2003
CAT	A180	6,709,909 B2	03/23/2004	Mizuno et al.			05/19/2003
CAT	A181	6,713,326 B2	03/30/2004	Cheng et al.			03/04/2003
CAT	A182	2001/0003364	06/14/2001	Sugawara et al.			12/08/2000
CAT	A183	2001/0007789 A1	07/12/2001	Aspar et al.			02/26/2001
CAT	A184	2002/0043660	04/18/2002	Yamazaki et al.			06/25/2001
CAT	A185	2002/052084	05/02/2002	Fitzgerald			05/16/2001
CAT	A186	2002/096717	07/25/2002	Chu et al.			01/25/2001
CAT	A187	2002/0100942	08/01/2002	Fitzgerald et al.			08/01/2002
CAT	A188	2002/0123167	09/05/2002	Fitzgerald			07/16/2001
CAT	A189	2002/0123183	09/05/2002	Fitzgerald			07/16/2001
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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
CAT	A190	2002/0123197	09/05/2002	Fitzgerald et al.			06/19/2001
CAT	A191	2002/0125471	09/12/2002	Fitzgerald et al.			12/04/2001
CAT	A192	2002/0125497	09/12/2002	Fitzgerald			07/16/2001
CAT	A193	2002/0168864	11/14/2002	Cheng et al.			04/04/2002
CAT	A194	2003/0003679	01/02/2003	Doyle et al.			06/29/2001
CAT	A195	2003/0013305 A1	01/16/2003	Sugii et al.			6/17/2002
CAT	A196	2003/0013323	01/16/2003	Hammond et al.			6/14/2002
CAT	A197	2003/0025131	02/06/2003	Lee et al.			08/02/2002
CAT	A198	2003/0034529	02/20/2003	Fitzgerald et al.			10/08/2002
CAT	A199	2003/0057439	03/27/2003	Fitzgerald			08/09/2002
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CAT	B2	0 514 018	11/19/1992	EP				No	Yes
CAT	B3	0 587 520	03/16/1994	EP				No	Yes
CAT	B4	0 683 522	11/22/1995	EP				No	Yes
CAT	B5	0 828 296	03/11/1998	EP				No	Yes
CAT	B6	0 829 908	03/18/1998	EP				No	Yes
CAT	B7	0 838 858	04/29/1998	EP				No	No

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(AT)	B8	1 020 900	07/19/2000	EP				No	Yes
(AT)	B9	1 174 928	01/23/2002	EP				No	Yes
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(AT)	B11	4-307974	10/30/1992	JP				No	No
(AT)	B12	5-166724	07/03/1993	JP				No	Abstract Only
(AT)	B13	6-177046	06/24/1994	JP				No	Abstract Only
(AT)	B14	7-106446	04/21/1995	JP				No	No
(AT)	B15	7-240372	09/12/1995	JP				No	Abstract Only
(AT)	B16	10-270685	10/09/1998	JP				No	Yes
(AT)	B17	11-233744	08/27/1999	JP				No	No
(AT)	B18	2000-021783	01/21/2000	JP				No	Yes
(AT)	B19	2000-31491	01/28/2000	JP				No	No
(AT)	B20	2001319935	05/11/2000	JP				Yes	Yes
(AT)	B21	2002-076334	03/15/2002	JP				No	Yes
(AT)	B22	2002-164520	06/07/2002	JP				No	Yes
(AT)	B23	2002-289533	10/04/2002	JP				No	Yes
(AT)	B24	WO 98/59365	12/30/1998	PCT				No	Yes
(AT)	B25	WO 99/53539	10/21/1999	PCT				No	Yes
(AT)	B26	WO 00/48239	08/17/2000	PCT				No	Yes
(AT)	B27	WO 01/54202	07/26/2001	PCT				No	Yes
(AT)	B28	WO 01/99169A2	12/27/2001	PCT				No	Yes
(AT)	B29	WO 02/15244 A2	02/21/2002	PCT				No	Yes
(AT)	B30	WO 02/27783 A1	04/04/2002	PCT				No	Yes
(AT)	B31	WO 02/071495A1	09/12/2002	PCT				No	Yes
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		APPLICANTS: Cheng et al.
		SERIAL NO.: 10/802,185
		FILING DATE: March 17, 2004
		GROUP: Not yet assigned 2813

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GAT	B33	WO 00/54338	09/14/2000	WO				No	Yes
CAT	B34	WO 01/022482	03/29/2001	WO				No	Yes
CAT	B35	WO 01/93338	12/06/2001	WO				No	Yes
VAT	B36	WO 02/13262	02/14/2002	WO				No	Yes
CAT	B37	WO 02/47168	06/13/2002	WO				No	Yes
VAT	B38	WO 02/071488	09/12/2002	WO				No	Yes
VAT	B39	WO 02/071491	09/12/2002	WO				No	Yes
VAT	B40	WO 04/006311 A2	01/15/2004	WO			07/09/2003		YES
VAT	B41	WO 04/006326 A1	01/15/2004	WO			07/09/2003		YES
VAT	B42	WO 04/006327 A2	01/15/2004	WO			07/09/2003		YES
CAT	B43	WO 04/019403 A2	03/04/2004	WO			08/26/2003		YES
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VAT	C2	Armstrong et al., "Design of Si/SiGe Heterojunction Complementary Metal-Oxide-Semiconductor Transistors," IEDM Technical Digest (1995) pp. 761-764.	
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FORM PTO - 1449 INFORMATION DISCLOSURE STATEMENT		ATTY DOCKET NO.: ASC-025DVC1 APPLICANTS: Cheng <i>et al.</i> SERIAL NO.: 10/802,185 FILING DATE: March 17, 2004 GROUP: Not yet assigned 2813
OTHER ART, JOURNAL ARTICLES, ETC.		
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